

MITSUBISHI IGBT MODULES  
**CM150DU-12F**

HIGH POWER SWITCHING USE

**CM150DU-12F**



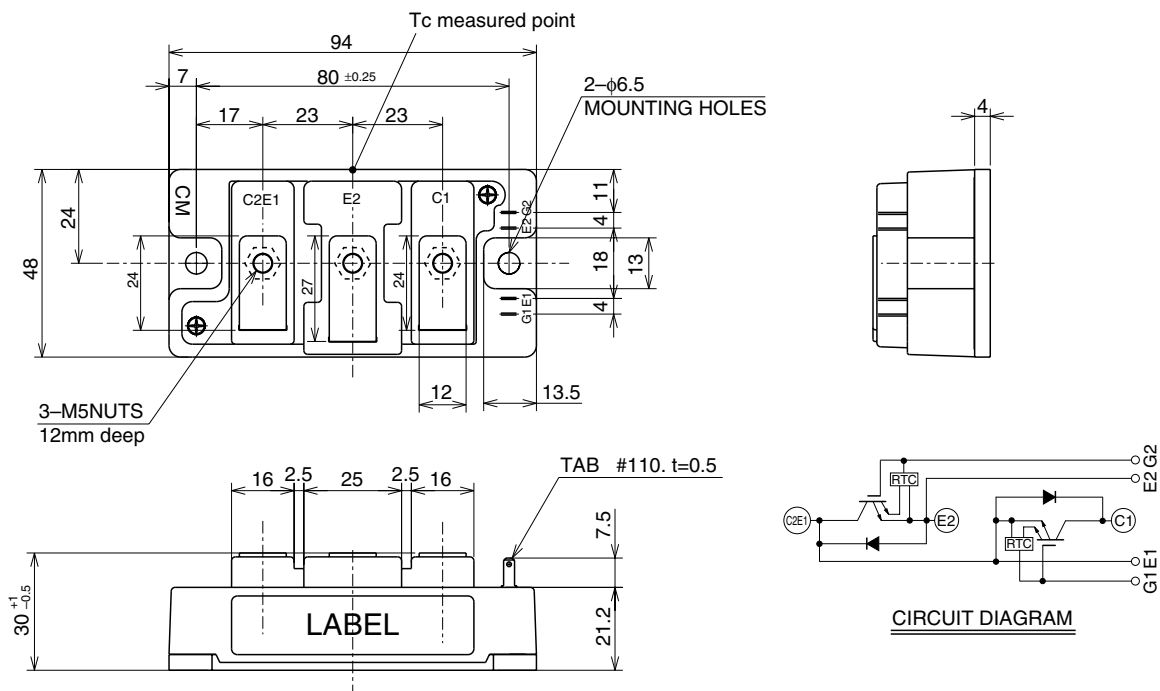
- Ic ..... 150A
- VCES ..... 600V
- Insulated Type
- 2-elements in a pack

**APPLICATION**

General purpose inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



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### MAXIMUM RATINGS (T<sub>j</sub> = 25°C, unless otherwise specified)

| Symbol                   | Parameter                     | Conditions                                        | Ratings    | Unit  |
|--------------------------|-------------------------------|---------------------------------------------------|------------|-------|
| V <sub>CES</sub>         | Collector-emitter voltage     | G-E Short                                         | 600        | V     |
| V <sub>GES</sub>         | Gate-emitter voltage          | C-E Short                                         | ±20        | V     |
| I <sub>C</sub>           | Collector current             | T <sub>C</sub> = 25°C                             | 150        | A     |
| I <sub>CM</sub>          |                               | Pulse (Note 2)                                    | 300        | A     |
| I <sub>E</sub> (Note 1)  | Emitter current               | T <sub>C</sub> = 25°C                             | 150        | A     |
| I <sub>EM</sub> (Note 1) |                               | Pulse (Note 2)                                    | 300        | A     |
| P <sub>C</sub> (Note 3)  | Maximum collector dissipation | T <sub>C</sub> = 25°C                             | 520        | W     |
| T <sub>j</sub>           | Junction temperature          |                                                   | −40 ~ +150 | °C    |
| T <sub>stg</sub>         | Storage temperature           |                                                   | −40 ~ +125 | °C    |
| V <sub>iso</sub>         | Isolation voltage             | Charged part to base plate, f = 60Hz, AC 1 minute | 2500       | Vrms  |
| —                        | Torque strength               | Main terminals M5 screw                           | 2.5 ~ 3.5  | N • m |
| —                        |                               | Mounting M6 screw                                 | 3.5 ~ 4.5  | N • m |
| —                        | Weight                        | Typical value                                     | 310        | g     |

### ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise specified)

| Symbol                   | Parameter                            | Test conditions                                                                                                                           | Limits |      |        | Unit |
|--------------------------|--------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------|--------|------|--------|------|
|                          |                                      |                                                                                                                                           | Min.   | Typ. | Max.   |      |
| I <sub>CES</sub>         | Collector cutoff current             | V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V                                                                                 | —      | —    | 1      | mA   |
| V <sub>GE(th)</sub>      | Gate-emitter threshold voltage       | I <sub>C</sub> = 15mA, V <sub>CE</sub> = 10V                                                                                              | 5      | 6    | 7      | V    |
| I <sub>GES</sub>         | Gate leakage current                 | ±V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V                                                                                | —      | —    | 20     | μA   |
| V <sub>CE(sat)</sub>     | Collector-emitter saturation voltage | I <sub>C</sub> = 150A, V <sub>GE</sub> = 15V                                                                                              | —      | 1.6  | 2.2    | V    |
|                          |                                      | T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 125°C                                                                                           |        | 1.6  | —      |      |
| C <sub>ies</sub>         | Input capacitance                    | V <sub>CE</sub> = 10V<br>V <sub>GE</sub> = 0V                                                                                             | —      | —    | 41     | nF   |
| C <sub>oes</sub>         | Output capacitance                   |                                                                                                                                           | —      | —    | 2.7    | nF   |
| C <sub>res</sub>         | Reverse transfer capacitance         |                                                                                                                                           | —      | —    | 1.5    | nF   |
| Q <sub>G</sub>           | Total gate charge                    | V <sub>CC</sub> = 300V, I <sub>C</sub> = 150A, V <sub>GE</sub> = 15V                                                                      | —      | 930  | —      | nC   |
| t <sub>d(on)</sub>       | Turn-on delay time                   | V <sub>CC</sub> = 300V, I <sub>C</sub> = 150A<br>V <sub>GE</sub> = ±15V<br>R <sub>G</sub> = 4.2Ω, Inductive load<br>I <sub>E</sub> = 150A | —      | —    | 120    | ns   |
| t <sub>r</sub>           | Turn-on rise time                    |                                                                                                                                           | —      | —    | 100    | ns   |
| t <sub>d(off)</sub>      | Turn-off delay time                  |                                                                                                                                           | —      | —    | 350    | ns   |
| t <sub>f</sub>           | Turn-off fall time                   |                                                                                                                                           | —      | —    | 250    | ns   |
| t <sub>rr</sub> (Note 1) | Reverse recovery time                |                                                                                                                                           | —      | —    | 150    | ns   |
| Q <sub>rr</sub> (Note 1) | Reverse recovery charge              |                                                                                                                                           | —      | 2.8  | —      | μC   |
| V <sub>EC</sub> (Note 1) | Emitter-collector voltage            | I <sub>E</sub> = 150A, V <sub>GE</sub> = 0V                                                                                               | —      | —    | 2.6    | V    |
| R <sub>th(j-c)Q</sub>    | Thermal resistance*1                 | IGBT part (1/2 module)                                                                                                                    | —      | —    | 0.24   | K/W  |
| R <sub>th(j-c)R</sub>    |                                      | FWDi part (1/2 module)                                                                                                                    | —      | —    | 0.47   | K/W  |
| R <sub>th(c-f)</sub>     | Contact thermal resistance           | Case to heat sink, Thermal compound applied*2 (1/2 module)                                                                                | —      | 0.07 | —      | K/W  |
| R <sub>th(j-c')Q</sub>   | Thermal resistance                   | Case temperature measured point is just under the chips                                                                                   | —      | —    | 0.19*3 | K/W  |
| R <sub>G</sub>           | External gate resistance             |                                                                                                                                           | 4.2    | —    | 42     | Ω    |

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub>, Q<sub>rr</sub> & die/dt represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

\*1 : Case temperature (T<sub>C</sub>) measured point is indicated in OUTLINE DRAWING.

\*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

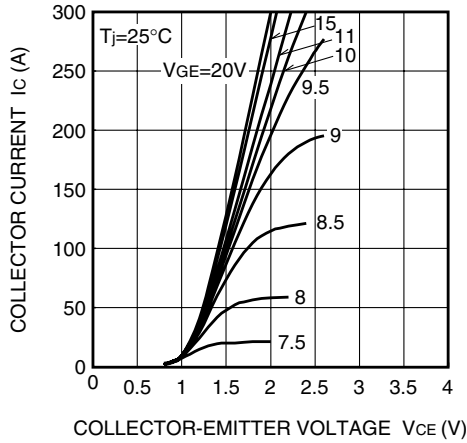
\*3 : If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

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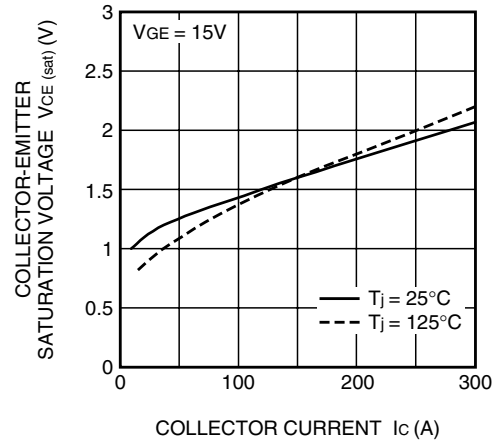
HIGH POWER SWITCHING USE

## PERFORMANCE CURVES

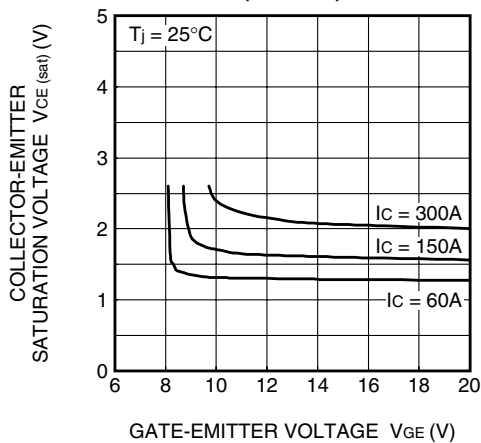
OUTPUT CHARACTERISTICS  
(TYPICAL)



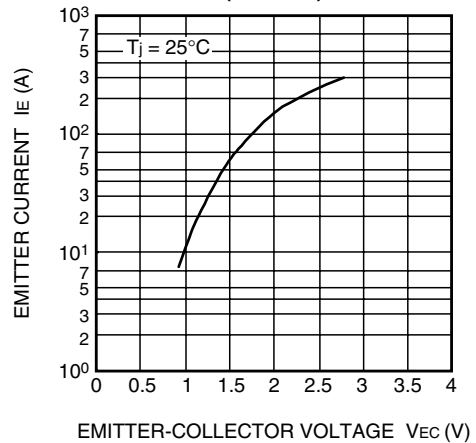
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



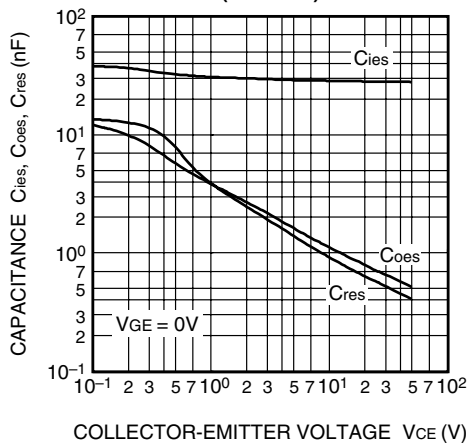
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



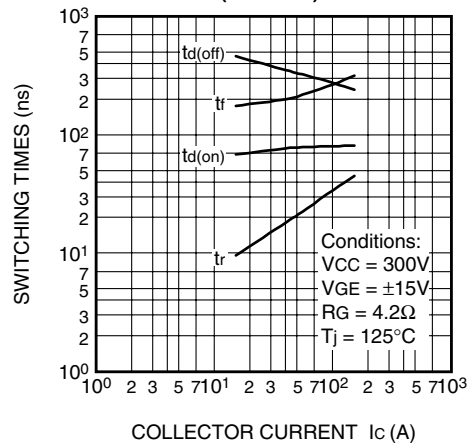
FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



CAPACITANCE- $V_{ce}$   
CHARACTERISTICS  
(TYPICAL)



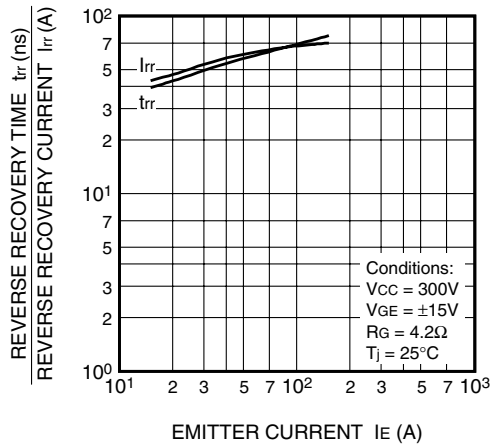
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)



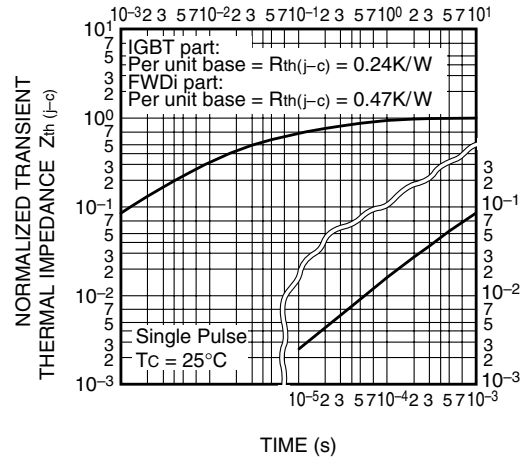
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HIGH POWER SWITCHING USE

REVERSE RECOVERY CHARACTERISTICS  
OF FREE-WHEEL DIODE  
(TYPICAL)



TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS  
(IGBT part & FWDi part)



GATE CHARGE  
CHARACTERISTICS  
(TYPICAL)

